

#### N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BV <sub>DSS</sub>	RDS(on)	I <sub>D</sub> T <sub>A</sub> = +25°C
20V	$3.0\Omega$ @ V <sub>GS</sub> = $4.5V$	240mA
200	6.0Ω @ V <sub>GS</sub> = 1.8V	180mA

### Description

This new generation MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

# **Applications**

- DC-DC converters
- Power management functions

### **Features and Benefits**

- N-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package, 0.4mm Maximum Package
- **ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotive-

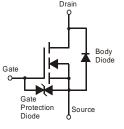
This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/quality/product-definitions/

### Mechanical Data

- Package: X2-DFN1006-3
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e4)
- Weight: 0.001 grams (Approximate)







**Equivalent Circuit** 

Top View

### **Ordering Information** (Note 4)

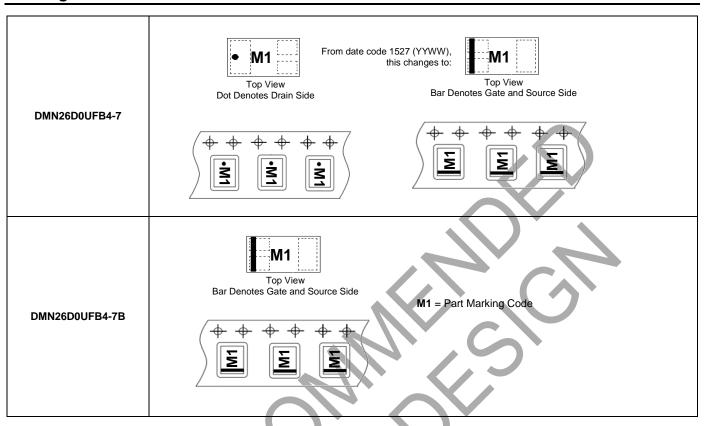
Part Number Pac	Package	Packing		
	rackaye	Qty.	Carrier	
DMN26D0UFB4-7	X2-DFN1006-3	3,000	Tape & Reel	
DMN26D0UFB4-7B	X2-DFN1006-3	10,000	Tape & Reel	

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. Notes:

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and
- <1000ppm antimony compounds. 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



# **Marking Information**



### **Maximum Ratings** (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain Source Voltage			V <sub>DSS</sub>	20	V
Gate-Source Voltage			Vgss	±10	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 4.5V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	lo	240 190	mA
Continuous Drain Current (Note 5) V <sub>GS</sub> = 1.8V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	lo	180 140	mA
Pulsed Drain Current - tp = 10μs			I <sub>DM</sub>	805	mA

# Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5) @T <sub>A</sub> = +25°C	PD	350	mW
Thermal Resistance, Junction to Ambient (Note 5)	Reja	357	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Note: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

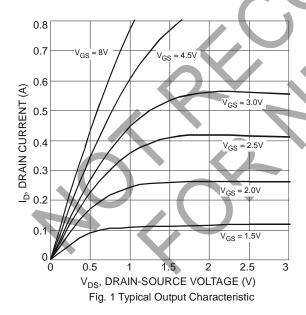


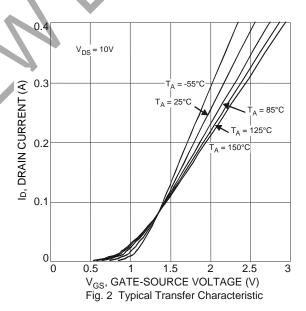
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BVDSS	20	_	_	V	$V_{GS} = 0V, I_{D} = 100\mu A$
Zero Gate Voltage Drain Current @ T <sub>C</sub> = +25°C	IDSS		_	500	nA	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V
Gate-Body Leakage	I <sub>GSS</sub>	_	_	±1 ±100	μA nA	$V_{GS} = \pm 10V, V_{DS} = 0V$ $V_{GS} = \pm 5V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)			•	•		
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.6		0.9	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
		_	1.8	3.0		Vgs = 4.5V, ID = 100mA
Static Drain-Source On-Resistance	Proconi	_	2.5	4.0	Ω	$V_{GS} = 2.5V, I_D = 50mA$
otatic Brain Godice on Nesistance	RDS(ON)	_	3.4	6.0	12	$V_{GS} = 1.8V, I_D = 20mA$
		_	4.7	10.0		$V_{GS} = 1.5V, I_{D} = 10mA$
Forward Transconductance	Y <sub>fs</sub>	180	242	_	mS	$V_{DS} = 10V, I_{D} = 0.1A$
Source-Drain Diode Forward Voltage	$V_{SD}$	0.5	4	1.4	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 7)	•					
Input Capacitance	Ciss		14.1	28.2	pF	
Output Capacitance	Coss		2.9	5.8	pF	Vps = 15V, Vgs = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss		1.6	3.2	pF	1 = 1.0WII IZ
SWITCHING CHARACTERISTICS (Note 7)					,	
Turn-On Delay Time	tD(ON)	1-	3.8			
Rise Time	t <sub>R</sub>	1	7.9		, , ,	Vgs = 4.5V, VDD = 10V
Turn-Off Delay Time	tD(OFF)	<u> </u>	13.4		ns	$I_D = 200 \text{mA}, R_G = 2.0 \Omega$
Fall Time	tr	_	15.2			

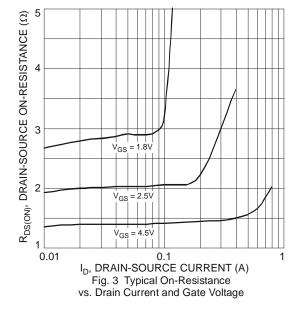
Notes:

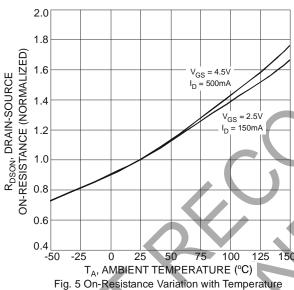
- 6. Short duration pulse test used to minimize self-heating effect.
- 7. Guaranteed by design. Not subject to product testing.











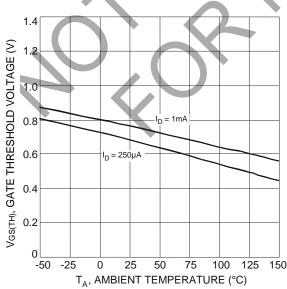
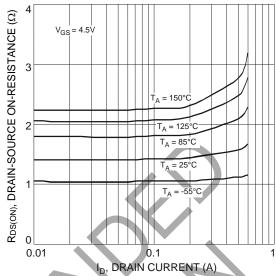


Fig. 7 Gate Threshold Variation vs. Ambient Temperature



I<sub>D</sub>, DRAIN CURRENT (A)
Fig. 4 Typical On-Resistance
vs. Drain Current and Temperature

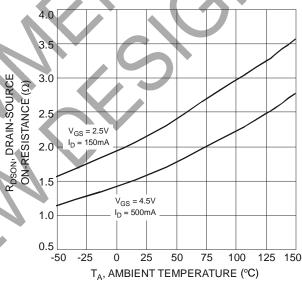


Fig. 6 On-Resistance Variation with Temperature

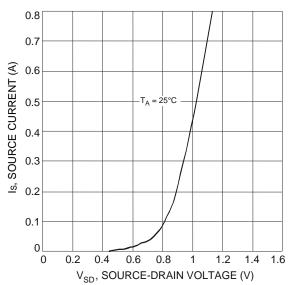
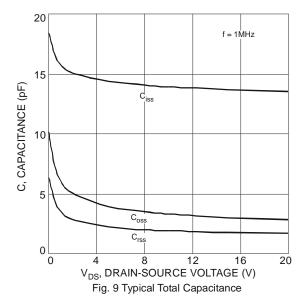


Fig. 8 Diode Forward Voltage vs. Current





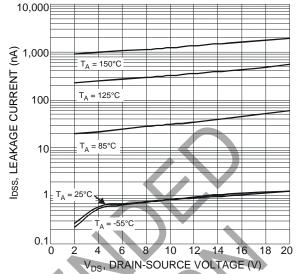


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

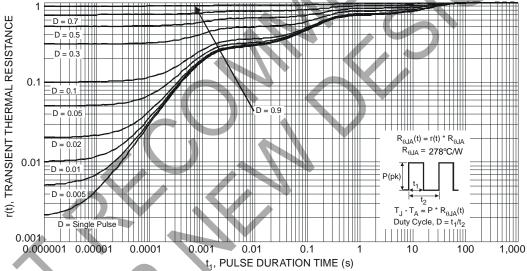


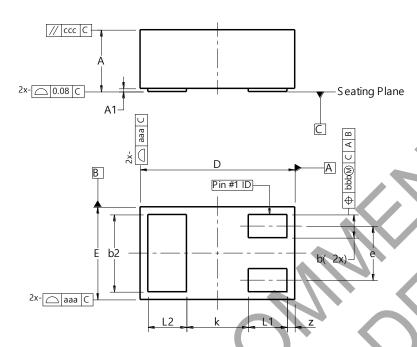
Fig. 11 Transient Thermal Response



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### X2-DFN1006-3

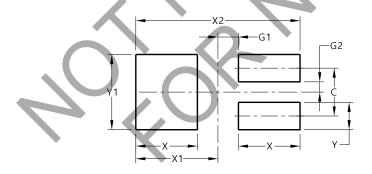


X2-DFN1006-3					
Dim	Min	Max	Тур		
A	l	0.40			
A1	0.00	0.05	0.03		
b	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.05	1.00		
E	0.55	0.65	0.60		
е		•	0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
k	1	١	0.40		
Z	0.02	0.08	0.05		
aaa	0.15				
bbb	0.05				
CCC	0.05				
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

# X2-DFN1006-3



Dimensions	Value (in mm)
С	0.350
G1	0.150
G2	0.075
Х	0.450
X1	0.600
X2	1.200
Y	0.200
Y1	0.550



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